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(54) **Title:** METHOD FOR DISSOLVING A BURIED OXIDE IN A SILICON-ON-INSULATOR WAFER

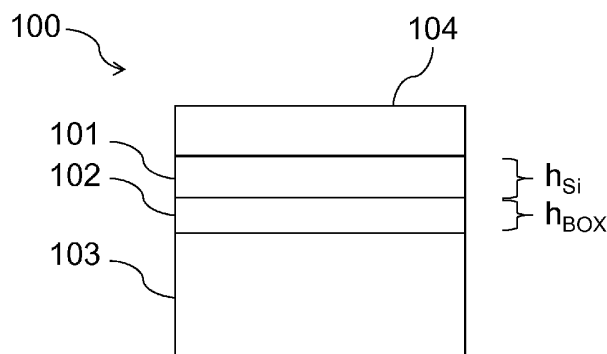


FIG. 1

(57) **Abstract:** The present invention relates to a method for dissolving a buried oxide in a silicon-on-insulator wafer, comprising providing a silicon-on-insulator wafer (100, 300, 400, 500) having a silicon layer (101, 301, 401, 501) attached to a carrier substrate (103, 303, 403, 503) via a buried oxide layer (102, 302, 402, 502), and annealing said silicon-on-insulation wafer (100, 300, 400, 500) to at least partially dissolve the buried oxide layer (102, 302, 402, 502). The inventive method further comprises a step of providing an oxygen scavenging layer (104, 304, 404, 504) on or over the silicon layer (101, 301, 401, 501) before the annealing step.



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